

HIGH POWER DPDT SWITCH GaAs MMIC

■ FEATURES

- AEC-Q100 grade 2 qualified
- Low voltage operation V_{DD} = 2.7 V typ.
- Logic control voltage V_{CTL}(H) = 1.35 to 5.0 V
- Low insertion loss

0.25 dB typ. @ f = 900 MHz, P_{IN} = +35 dBm 0.35 dB typ. @ f = 1900 MHz, P_{IN} = +33 dBm 0.45 dB typ. @ f = 2700 MHz, P_{IN} = +27 dBm

Low harmonics

2fo = -89 dBm typ. @ f = 786.5 MHz, P_{IN} = +23 dBm 3fo = -89 dBm typ. @ f = 710 MHz, P_{IN} = +23 dBm

High power handling

 $P_{-0.1dB}$ = +36 dBm min.

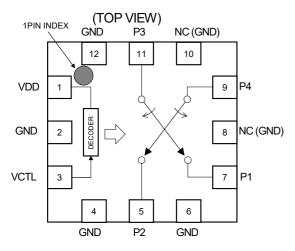
 Package with wettable flank EQFN12-ET (2.0 x 2.0 x 0.78 mm typ., pin pitch 0.5 mm)

• RoHS compliant and Halogen Free, MSL1

■ APPLICATION

- eCall
- Telematics
- Antenna swapping, general purpose switching applications
- LTE, UMTS, CDMA, GSM systems

■ **BLOCK DIAGRAM** (EQFN12-ET)



■ GENERAL DESCRIPTION

The NJG1812AMET-A is a GaAs DPDT switch MMIC suitable for antenna swapping of LTE/UMTS/CDMA/GSM applications.

This switch features very low insertion loss, low distortion and excellent linearity performance with 1.8 V 1bit control voltage at high frequency up to 3 GHz.

Integrated ESD protection device on each port achieves excellent ESD robustness. No DC blocking capacitors are required for all RF ports unless DC is biased externally.

EQFN12-ET package with wettable flank structure corresponds to Automated Optical Inspection (AOI).

■ TRUTH TABLE

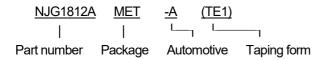
"H" =
$$V_{CTL}(H)$$
, "L" = $V_{CTL}(L)$

Vctl	Path
1	P1-P4
L	P2-P3
Н	P1-P3
	P2-P4

■ PIN CONFIGURATION

PIN NO.	SYMBOL	DESCRIPTION
1	VDD	Voltage supply terminal
2	GND	Ground terminal
3	VCTL	Control signal input
3	VCIL	terminal.
4	GND	Ground terminal
5	P2	RF input/output
6	GND	Ground terminal
7	P1	RF input/output
8	NC (CND)	No connected terminal
· · · · · · · · · · · · · · · · · · ·	NC (GND)	(Connect to ground)
9	P4	RF input/output
10	NC (CND)	No connected terminal
	NC (GND)	(Connect to ground)
11	P3	RF input/output
12	GND	Ground terminal
Exposed pad	GND	Ground terminal

■ PRODUCT NAME INFORMATION



■ ORDERING INFORMATION

PART NUMBER	PACKAGE OUTLINE	RoHS	HALOGEN- FREE	TERMINAL FINISH	MARKING	WEIGHT (mg)	MOQ (pcs.)
NJG1812AMET-A	EQFN12-ET	Yes	Yes	SnBi	1812 A A	8.5	3,000

■ ABSOLUTE MAXIMUM RATINGS

(General conditions: $T_a = 25^{\circ}C$, $Z_s = Z_l = 50 \Omega$)

	(0	cricial conditions. Ta 20 0,	2s 21 00 32)
PARAMETER	SYMBOL	RATINGS	UNIT
RF Input Power	P _{IN}	+38(1)	dBm
Supply Voltage	V_{DD}	5.0	V
Control Voltage	V _{CTL} 5.0		V
Power Dissipation ⁽²⁾	PD	1400	mW
Operating Temperature	Topr	-40 to +105	°C
Storage Temperature	T _{stg}	-55 to +150	°C

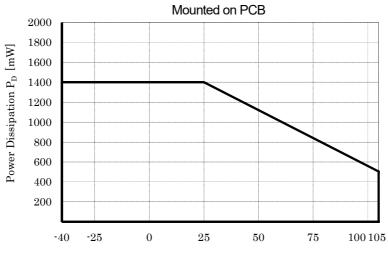
^{(1):} $V_{DD} = 2.7 \text{ V}$, ON port

■ POWER DISSIPATION VS.AMBIENT TEMPERATURE

Please, refer to the following Power Dissipation and Ambient Temperature.

(Please note the surface mount package has a small maximum rating of Power Dissipation [P_D], a special attention should be paid in designing of thermal radiation.)

Power Dissipation—Ambient Temperature Characteristic



Ambient Temperature $Ta[^{\circ}C]$

Nisshinbo Micro Devices Inc.

^{(2):} Four-layer FR4 PCB with through-hole (101.5 x 114.5 mm), Tj = 150°C

■ ELECTRICAL CHARACTERISTICS 1 (DC CHARACTERISTICS)

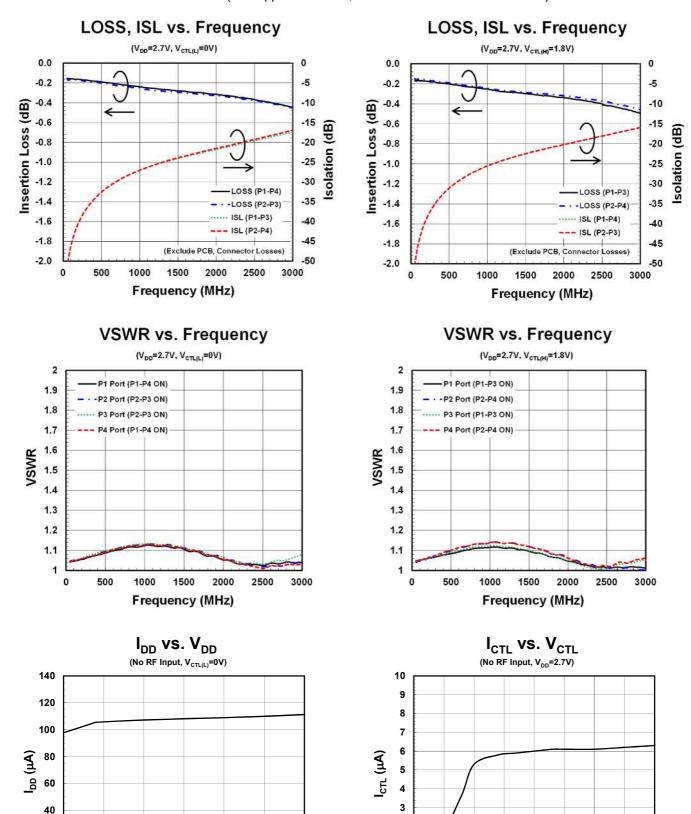
(General conditions: $T_a = 25^{\circ}C$, $Z_s = Z_l = 50 \Omega$, with application circuit)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V _{DD}		2.4	2.7	5.0	V
Operating Current	I _{DD}	No RF input	-	90	180	μΑ
Control Voltage (LOW)	Vctl(L)		0	-	0.45	V
Control Voltage (HIGH)	V _{CTL} (H)		1.35	1.8	5.0	V
Control Current	ICTL	V _{CTL} (H) = 1.8V	1	4	10	μΑ

■ ELECTRICAL CHARACTERISTICS 2 (RF CHARACTERISTICS)

 $(General \ conditions: \ T_a = +25^{\circ}C, \ Z_s = Z_l = 50 \ \Omega, \ V_{DD} = 2.7 \ V, \ V_{CTL}(H) = 1.8 \ V, \ V_{CTL}(L) = 0 \ V, \ with \ application \ circuit)$

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
		f = 900 MHz, P _{IN} = +35 dBm	-	0.25	0.45		
Insertion Loss	LOSS	f = 1900 MHz, P _{IN} = +33 dBm	-	0.35	0.55	dB	
		f = 2700 MHz, P _{IN} = +27 dBm	-	0.45	0.65		
		f = 900 MHz, P _{IN} = +35 dBm	23	25	-		
Isolation	ISL	f = 1900 MHz, P _{IN} = +33 dBm	18	20	-	dB	
		f = 2700 MHz, P _{IN} = +27 dBm	15	17	-		
Input Power at 0.1dB Compression Point	P _{-0.1dB}	f = 2700 MHz	+36	-	-	dBm	
		$f = 900 \text{ MHz}, P_{IN} = +33 \text{ dBm}$	-	-	-40		
2nd Harmonics	2fo	f = 1900 MHz, P _{IN} = +30 dBm	-	-	-40	dBm	
ZHU HAITHOHICS	210	f = 2700 MHz, P _{IN} = +23 dBm	-	-	-60		
		f = 786.5 MHz, P _{IN} = +23 dBm	-	-89	-81		
		$f = 900 \text{ MHz}, P_{IN} = +33 \text{ dBm}$	-	-	-40	dBm	
		f = 1900 MHz, P _{IN} = +30 dBm	-	-	-40		
3rd Harmonics	3fo	$f = 2700 \text{ MHz}, P_{IN} = +23 \text{ dBm}$	-	-	-60		
		f = 710 MHz, P _{IN} = +23 dBm	-	-89	-81		
		f = 786.5 MHz, P _{IN} = +23 dBm	-	-89	-81		
2nd order intermodulation	IMD2	f_{TX} = 835 MHz, P_{TX} = +20 dBm, f_{jam} = 1715 MHz, P_{jam} = -15 dBm, f_{meas} = 880 MHz	-	-110	-105	dBm	
3rd order intermodulation	IMD3	f_{TX} = 835 MHz, P_{TX} = +20 dBm, f_{jam} = 790 MHz, P_{jam} = -15 dBm, f_{meas} = 880 MHz	-	-110	-105	dBm	
Triple Beat Ratio	TBR	$f_{TX}1 = 835.5 \text{ MHz}, P_{TX}1 = +21.5 \text{ dBm}, \\ f_{TX}2 = 836.5 \text{ MHz}, P_{TX}2 = +21.5 \text{ dBm}, \\ f_{jam} = 881.5 \text{ MHz}, P_{jam} = -30 \text{ dBm}, \\ f_{meas} = 881.5 \pm 1 \text{ MHz}$	-	93	-	dBc	
VSWR	VSWR	P1 to P4 Terminal, f = 2700 MHz	-	1.1	1.5	-	
Switching time	Tsw	50% V _{CTL} to 10/90% RF	-	1	5	μS	



20

0

2

2.5

3

3.5

 $V_{DD}(V)$

4.5

2

1

0

1.5

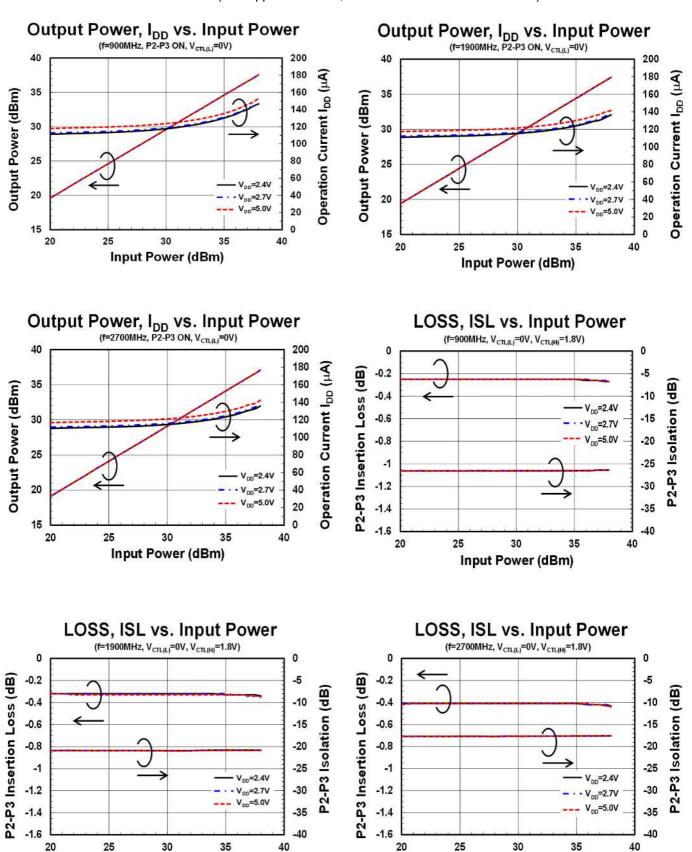
2

2.5

V_{CTL} (V)

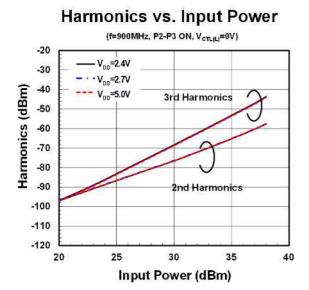
4.5

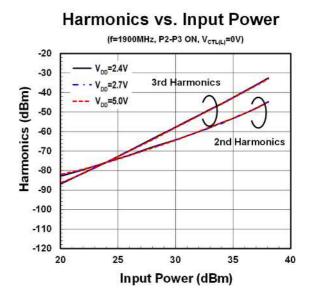
5

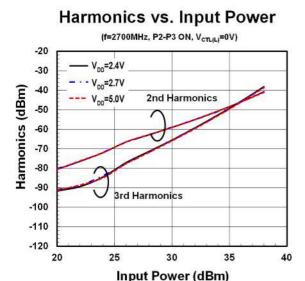


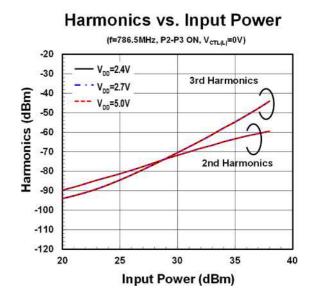
Input Power (dBm)

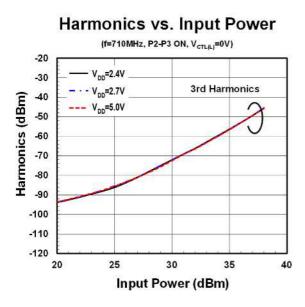
Input Power (dBm)

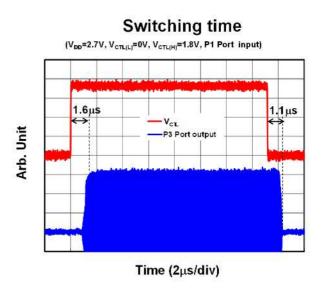




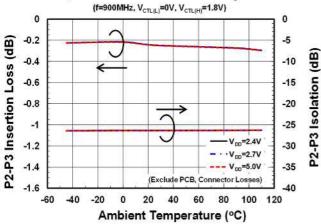




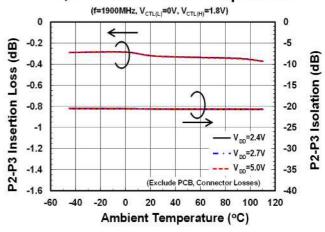




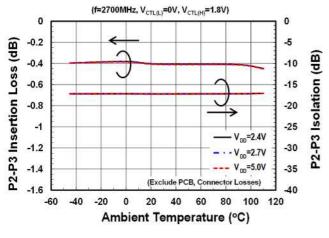




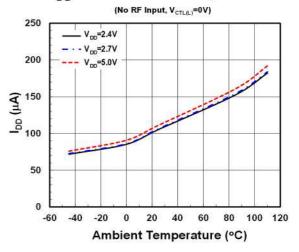
LOSS, ISL vs. Ambient Temperature



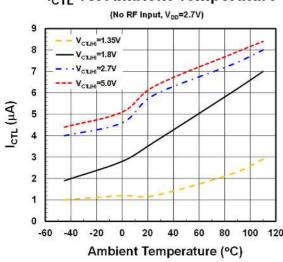
LOSS, ISL vs. Ambient Temperature



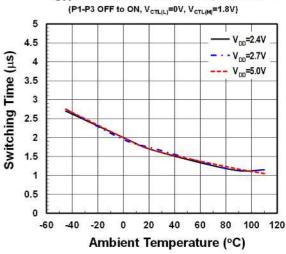
I_{DD} vs. Ambient Temperature



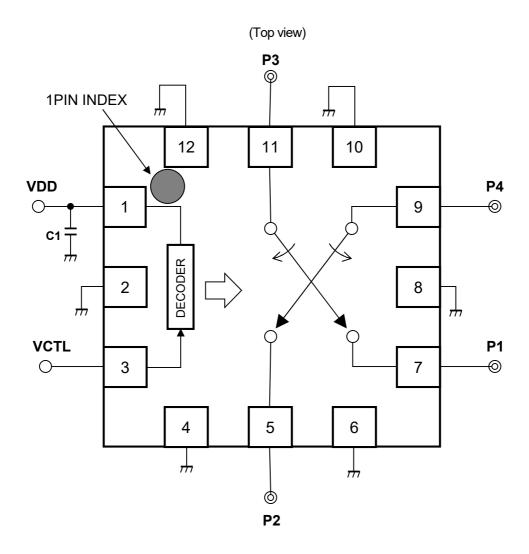
I_{CTL} vs. Ambient Temperature



T_{SW} vs. Ambient Temperature



■ APPLICATION CIRCUIT



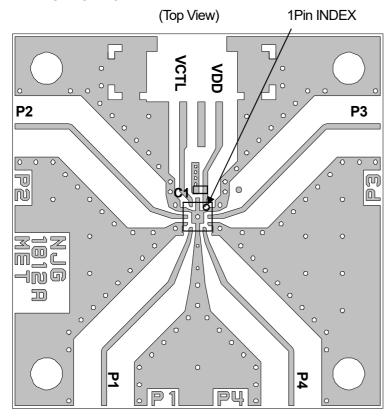
Note:

No DC blocking capacitors are required on all RF ports, unless DC is biased externally.

■ PARTS LIST

Part ID	Value	Notes
C1	1000 pF	MURATA (GRM15)

■ EVALUATION BOARD



PCB (FR-4):

t = 0.2 mm

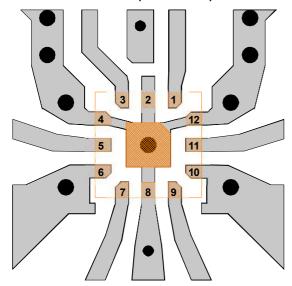
MICROSTRIP LINE WIDTH = 0.37 mm (Z_0 = 50 Ω)

PCB SIZE = 26 mm x 26 mm

Losses of PCB and connectors, Ta = +25°C

Frequency [GHz]	Loss [dB]
0.9	0.23
1.9	0.43
2.7	0.55

■ PCB LAYOUT GUIDELINE (EQFN12-ET)







PKG outline

- Ground via hole Diameter $\Phi = 0.3 \text{ mm}$
- Ground via holeDiameter Φ = 0.2 mm

PRECAUTIONS

- [1] For avoiding the degradation of RF performance, the bypass capacitor (C1) should be placed as close as possible to VDD terminal
- [2] For good RF performance, all GND terminals are must be connected to PCB ground plane of substrate, and through holes for GND should be placed near the IC.
- [3] Please connect Exposed PAD to PCB ground plane of substrate, and through holes for ground should be placed under the IC.

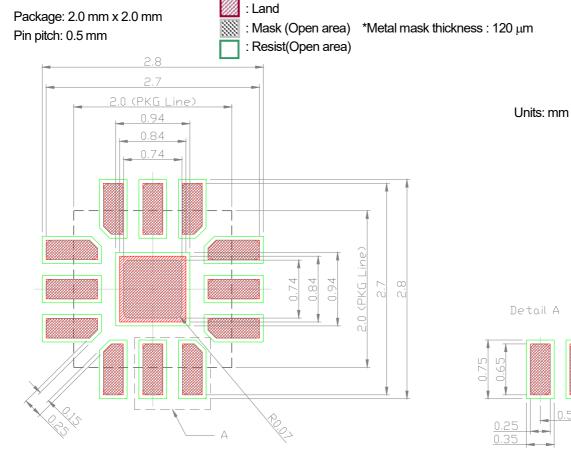
■ HANDLING PRECAUTIONS

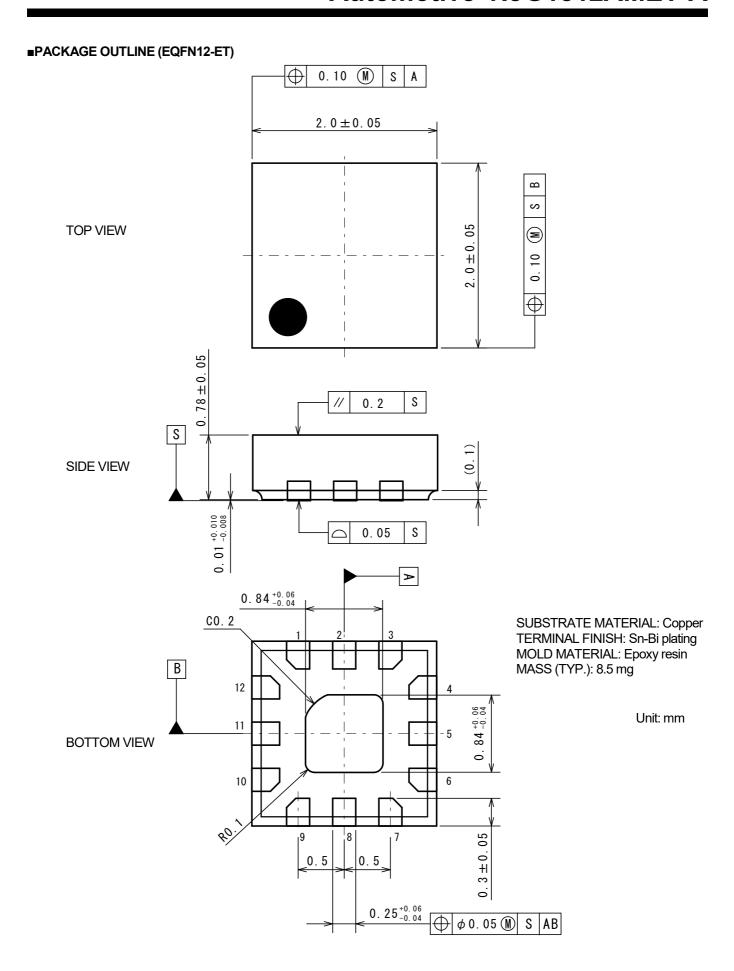
DINING	0) (1 4 1 2 0 1		ESD R	ATINGS	
PIN NO.	SYMBOL	Hur	nan Body Mod	del ⁽³⁾	Charged
Commo	Common terminal		VDD	I/O	Device Model ⁽⁴⁾
1	VDD	Class 2	COM.	-	Class C6
2	GND	COM.	Class 2	-	Class C6
3	VCTL	Class 2	Class 1C	Class 1C	Class C6
4	GND	COM.	Class 1C	-	Class C6
5	P2	Class 2	Class 1A	Class 2	Class C6
6	GND	COM.	Class 1A	•	Class C6
7	P1	Class 2	Class 1B	Class 2	Class C6
8	NC(GND)	COM.	Class 2	-	Class C6
9	P4	Class 2	Class 1C	Class 2	Class C6
10	NC(GND)	COM.	Class 1C	-	Class C6
11	P3	Class 2	Class 1B	Class 2	Class C6
12	GND	COM.	Class 1C	-	Class C6

- (3): According to JEDEC JS-001
- (4): According to JEDEC JS-002

CAUTION: This product may be damaged with electric static discharge (ESD) or spike voltage. Please handle with care to avoid these damages.

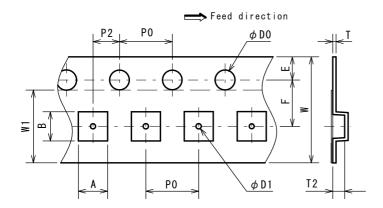
■ RECOMMENDED FOOTPRINT PATTERN (EQFN12-ET PACKAGE) <Reference>





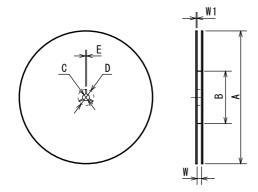
■ PACKING SPECIFICATION (EQFN12-ET)

TAPING DIMENSIONS UNIT: mm



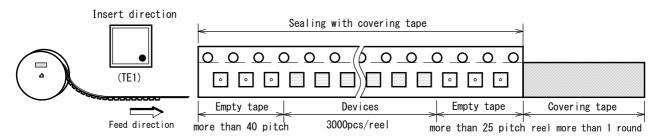
SYMBOL	DIMENSION	REMARKS
A	2. 26±0. 05	BOTTOM DIMENSION
В	2. 26±0. 05	BOTTOM DIMENSION
D0	1. 5 ^{+0. 1}	
D1	0. 5 +0.1	
Е	1.75±0.1	
F	3.5±0.05	
P0	4.0±0.1	
P1	4.0±0.1	
P2	2.0±0.05	
T	0. 25±0. 05	
T2	0.95±0.05	
W	8. 0 +0.3	
W1	5. 5	THICKNESS O. 1max

REEL DIMENSIONS

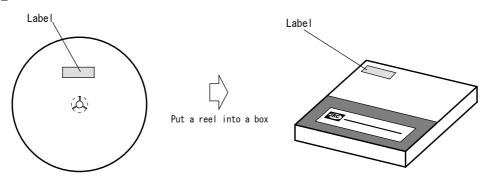


SYMBOL	DIMENSION
Α	ϕ 180 $^{0}_{-1.5}$
В	φ 60 ⁺¹ ₀
С	φ 13±0.2
D	ϕ 21±0.8
E	2±0.5
W	9 +1
W1	1. 2

TAPING STATE



PACKING STATE



■ REVISION HISTORY

Date	Revision	Changes			
	15.Oct.2021 Ver.1.1	Revised FEATURES			
		Revised TRUTH TABLE			
15 Oct 2021		Revised ELECTRICAL CHARACTERISTICS (No change for spec values)			
15.UCL.2021		Revised EVALUATION BOARD (added 1 pin index mark)			
		Revised PCB LAYOUT GUIDELINE			
		Revised CAUTION			
20.Aug.2020	Ver.1.0	New Release			

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 - Traffic control system
 - Combustion equipment

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 - 8-1. Quality Warranty Period

In the case of a product purchased through an authorized distributor or directly from us, the warranty period for this product shall be one (1) year after delivery to your company. For defective products that occurred during this period, we will take the quality warranty measures described in section 8-2. However, if there is an agreement on the warranty period in the basic transaction agreement, quality assurance agreement, delivery specifications, etc., it shall be followed.

8-2. Quality Warranty Remedies

When it has been proved defective due to manufacturing factors as a result of defect analysis by us, we will either deliver a substitute for the defective product or refund the purchase price of the defective product.

Note that such delivery or refund is sole and exclusive remedies to your company for the defective product.

8-3. Remedies after Quality Warranty Period

With respect to any defect of this product found after the quality warranty period, the defect will be analyzed by us. On the basis of the defect analysis results, the scope and amounts of damage shall be determined by mutual agreement of both parties. Then we will deal with upper limit in Section 8-2. This provision is not intended to limit any legal rights of your company.

- 9. Anti-radiation design is not implemented in the products described in this document.
- 10. The X-ray exposure can influence functions and characteristics of the products. Confirm the product functions and characteristics in the evaluation stage.
- 11. WLCSP products should be used in light shielded environments. The light exposure can influence functions and characteristics of the products under operation or storage.
- 12. Warning for handling Gallium and Arsenic (GaAs) products (Applying to GaAs MMIC, Photo Reflector). These products use Gallium (Ga) and Arsenic (As) which are specified as poisonous chemicals by law. For the prevention of a hazard, do not burn, destroy, or process chemically to make them as gas or power. When the product is disposed of, please follow the related regulation and do not mix this with general industrial waste or household waste.
- 13. Please contact our sales representatives should you have any questions or comments concerning the products or the technical information.



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